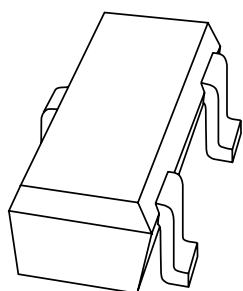


# DATA SHEET



## **PPTC143XK**

NPN resistor-equipped transistor;  
 $R1 = 4.7 \text{ k}\Omega$ ,  $R2 = 10 \text{ k}\Omega$

Product specification

2002 Jan 15

**NPN resistor-equipped transistor;  
R1 = 4.7 kΩ, R2 = 10 kΩ**

**PDTC143XK**

FEATURES

- Built-in bias resistors
- 250 mW total power dissipation
- Package size 2.9 × 1.5 × 1.15 mm
- Simplification of circuit design
- Reduces number of components and required PCB area.

APPLICATIONS

- General purpose switching and amplification
- Inverter and interface circuits
- Circuit driver.

DESCRIPTION

NPN resistor equipped transistor in a SOT346 (SC-59) plastic package.

MARKING

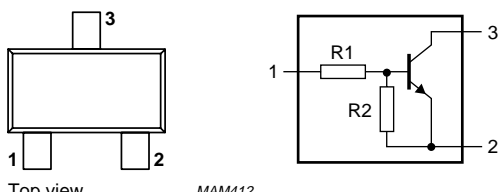
TYPE NUMBER	MARKING CODE
PDTC143XK	26

QUICK REFERENCE DATA

SYMBOL	PARAMETER	MAX.	UNIT
V <sub>CEO</sub>	collector-emitter voltage	50	V
I <sub>O</sub>	output current (DC)	100	mA
R1	bias resistor	4.7	kΩ
R2	bias resistor	10	kΩ

PINNING

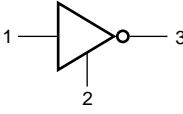
PIN	DESCRIPTION
1	base/input
2	emitter/ground (+)
3	collector/output



Top view

MAM412

Fig.1 Simplified outline (SOT346) and symbol.



MGA893 - 1

Fig.2 Equivalent inverter symbol.

NPN resistor-equipped transistor;  
 $R1 = 4.7\text{ k}\Omega$ ,  $R2 = 10\text{ k}\Omega$

PDTC143XK

## LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
$V_{CBO}$	collector-base voltage	open emitter	–	50	V
$V_{CEO}$	collector-emitter voltage	open base	–	50	V
$V_{EBO}$	emitter-base voltage	open collector	–	10	V
$V_i$	input voltage				
	positive		–	+20	V
	negative		–	–7	V
$I_o$	output current (DC)		–	100	mA
$I_{CM}$	peak collector current		–	100	mA
$P_{tot}$	total power dissipation	$T_{amb} \leq 25\text{ }^{\circ}\text{C}$ ; note 1	–	250	mW
$T_{stg}$	storage temperature		–65	+150	$^{\circ}\text{C}$
$T_j$	junction temperature		–	150	$^{\circ}\text{C}$
$T_{amb}$	operating ambient temperature		–65	+150	$^{\circ}\text{C}$

## Note

- For mounting conditions, see “*Thermal considerations and footprint design for SOT346 in the SC18 Data Handbook*”.

## THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
$R_{th\ j-a}$	thermal resistance from junction to ambient	in free air; note 1	500	K/W

## Note

- For mounting conditions, see “*Thermal considerations and footprint design for SOT346 in the SC18 Data Handbook*”.

NPN resistor-equipped transistor;  
 $R1 = 4.7 \text{ k}\Omega$ ,  $R2 = 10 \text{ k}\Omega$

PDTC143XK

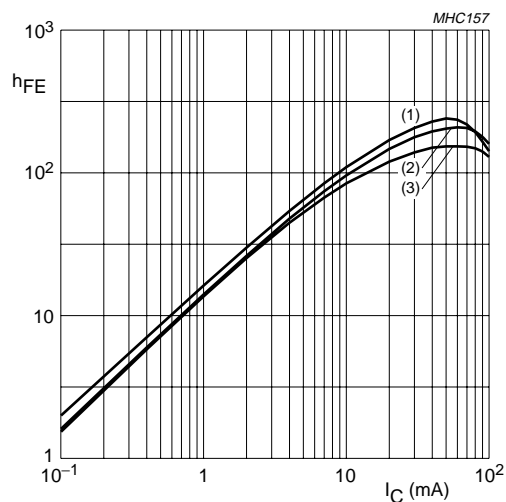
## CHARACTERISTICS

$T_{\text{amb}} = 25 \text{ }^{\circ}\text{C}$  unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
$I_{\text{CBO}}$	collector-base cut-off current	$V_{\text{CB}} = 50 \text{ V}$ ; $I_{\text{E}} = 0$	–	–	100	nA
$I_{\text{CEO}}$	collector-emitter cut-off current	$V_{\text{CE}} = 30 \text{ V}$ ; $I_{\text{B}} = 0$	–	–	1	$\mu\text{A}$
		$V_{\text{CE}} = 30 \text{ V}$ ; $I_{\text{B}} = 0$ ; $T_{\text{j}} = 150 \text{ }^{\circ}\text{C}$	–	–	50	$\mu\text{A}$
$I_{\text{EBO}}$	emitter-base cut-off current	$V_{\text{EB}} = 5 \text{ V}$ ; $I_{\text{C}} = 0$	–	–	0.6	mA
$h_{\text{FE}}$	DC current gain	$V_{\text{CE}} = 5 \text{ V}$ ; $I_{\text{C}} = 10 \text{ mA}$	50	–	–	
$V_{\text{CEsat}}$	collector-emitter saturation voltage	$I_{\text{C}} = 10 \text{ mA}$ ; $I_{\text{B}} = 0.5 \text{ mA}$	–	–	100	mV
$V_{\text{i(off)}}$	input off voltage	$V_{\text{CE}} = 5 \text{ V}$ ; $I_{\text{C}} = 100 \mu\text{A}$	–	–	0.3	V
$V_{\text{i(on)}}$	input on voltage	$V_{\text{CE}} = 0.3 \text{ V}$ ; $I_{\text{C}} = 20 \text{ mA}$	2.5	–	–	V
$R1$	input resistor		3.3	4.7	6.1	$\text{k}\Omega$
$\frac{R2}{R1}$	resistor ratio		1.7	2.1	2.6	
$C_{\text{c}}$	collector capacitance	$I_{\text{E}} = i_{\text{e}} = 0$ ; $V_{\text{CB}} = 10 \text{ V}$ ; $f = 1 \text{ MHz}$	–	–	3	pF

# NPN resistor-equipped transistor; R1 = 4.7 k $\Omega$ , R2 = 10 k $\Omega$

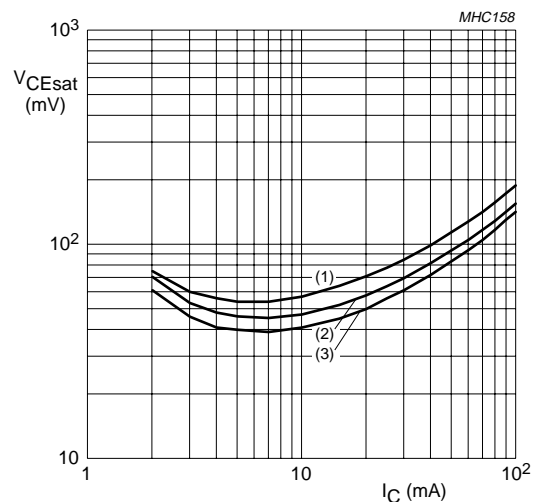
## PDTC143XK



$V_{CE} = 5$  V.

- (1)  $T_{amb} = 100^\circ\text{C}$ .
- (2)  $T_{amb} = 25^\circ\text{C}$ .
- (3)  $T_{amb} = -40^\circ\text{C}$ .

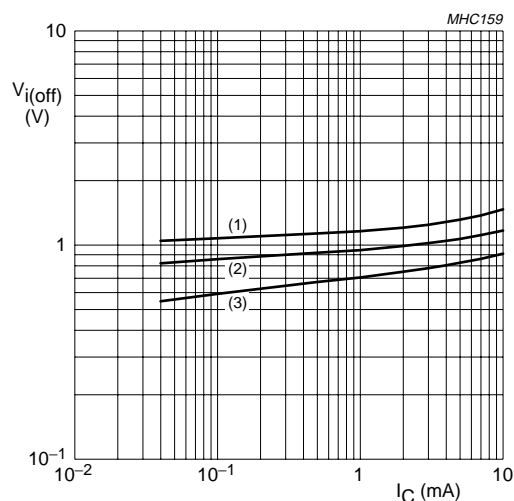
Fig.3 DC current gain as a function of collector current; typical values.



$I_C/I_B = 20$ .

- (1)  $T_{amb} = 100^\circ\text{C}$ .
- (2)  $T_{amb} = 25^\circ\text{C}$ .
- (3)  $T_{amb} = -40^\circ\text{C}$ .

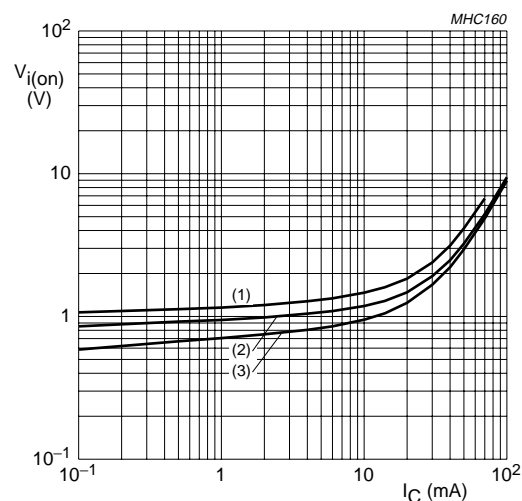
Fig.4 Collector-emitter saturation voltage as a function of collector current; typical values.



$V_{CE} = 5$  V.

- (1)  $T_{amb} = -40^\circ\text{C}$ .
- (2)  $T_{amb} = 25^\circ\text{C}$ .
- (3)  $T_{amb} = 100^\circ\text{C}$ .

Fig.5 Input-off voltage as a function of collector current; typical values.



$V_{CE} = 0.3$  V.

- (1)  $T_{amb} = -40^\circ\text{C}$ .
- (2)  $T_{amb} = 25^\circ\text{C}$ .
- (3)  $T_{amb} = 100^\circ\text{C}$ .

Fig.6 Input-on voltage as a function of collector current; typical values.

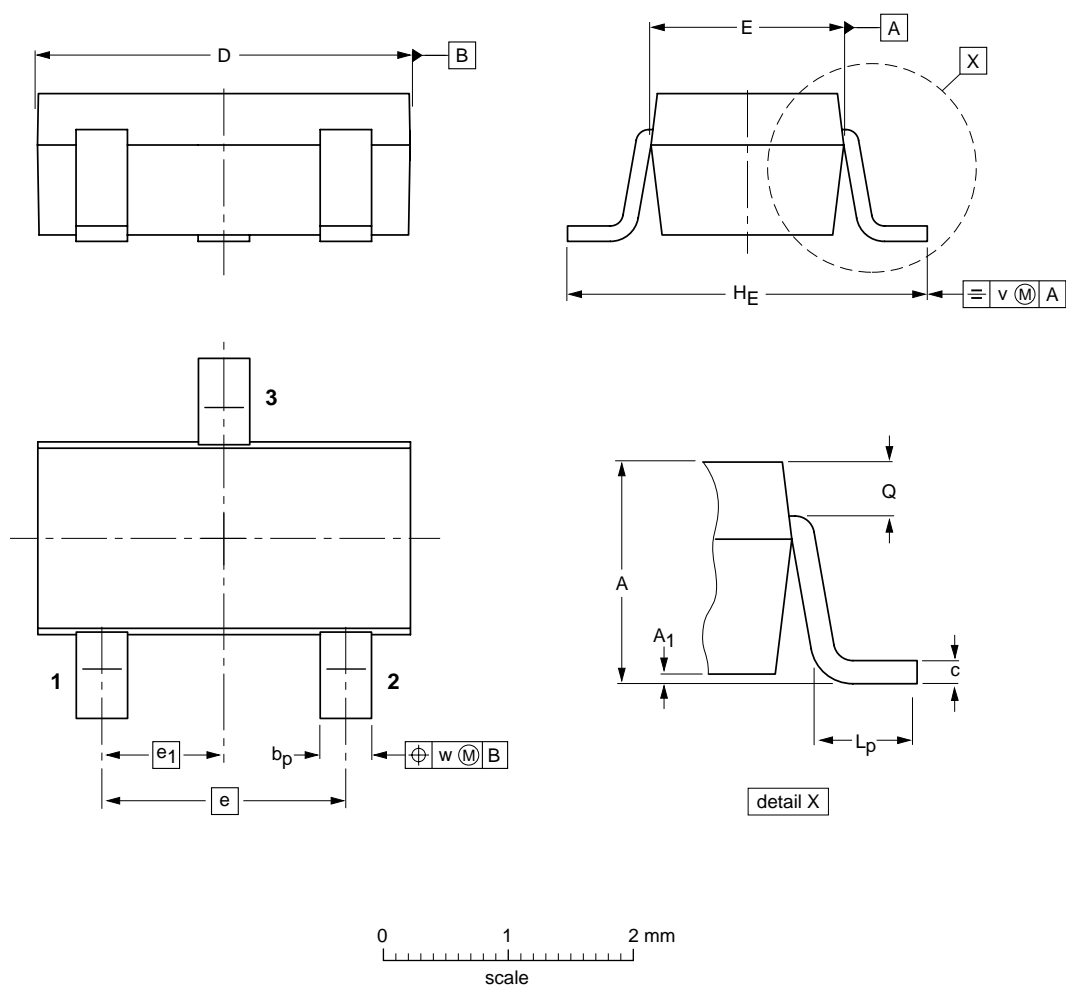
NPN resistor-equipped transistor;  
R1 = 4.7 kΩ, R2 = 10 kΩ

PDTC143XK

PACKAGE OUTLINE


Plastic surface mounted package; 3 leads

SOT346



DIMENSIONS (mm are the original dimensions)

UNIT	A	A <sub>1</sub>	b <sub>p</sub>	c	D	E	e	e <sub>1</sub>	H <sub>E</sub>	L <sub>p</sub>	Q	v	w
mm	1.3 1.0	0.1 0.013	0.50 0.35	0.26 0.10	3.1 2.7	1.7 1.3	1.9	0.95	3.0 2.5	0.6 0.2	0.33 0.23	0.2	0.2

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	EIAJ			
SOT346		TO-236	SC-59			98-07-17

NPN resistor-equipped transistor;  
R1 = 4.7 k $\Omega$ , R2 = 10 k $\Omega$

PDTC143XK

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